



### 20V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage 20 V Current 1A

#### **Features**

- RDS(ON), VGS@4.5V, ID@1.0A<150mΩ</li>
- RDS(ON) , VGS@2.5V, ID@0.7A<215mΩ</li>
- RDS(ON), VGS@1.8V, ID@0.3A<400mΩ</li>
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

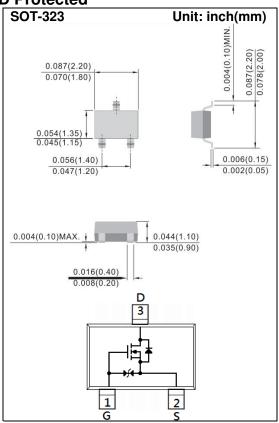
#### **Mechanical Data**

• Case: SOT-323 Package

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0002 ounces, 0.005 grams

Marking: C04



## Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	20	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 8	V
Continuous Drain Current		$I_D$	1	Α
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	4	Α
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	350	mW
	Derate above 25°C		2.8	mW/°C
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C
Typical Thermal resistance - Junction to Ambient (Note 3)		$R_{ heta JA}$	357	°C/W





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.5	8.0	1.0	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =4.5V, $I_D$ =1A	-	114	150	mΩ	
		$V_{GS}$ =2.5V, $I_{D}$ =0.7A	-	160	215		
		$V_{GS}=1.8V, I_{D}=0.3A$	-	280	400		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =20V, $V_{GS}$ =0V	-	0.01	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS}=\underline{+}8V, V_{DS}=0V$	-	<u>+</u> 2	<u>+</u> 10	uA	
Dynamic							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =1A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	1.6	-	nC	
Gate-Source Charge	$Q_{gs}$		-	0.3	-		
Gate-Drain Charge	$Q_gd$		-	0.41	-		
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,	-	92	-	pF	
Output Capacitance	Coss		-	25	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	9.1	-		
Switching							
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =10V, $I_{D}$ =1A, $V_{GS}$ =4.5V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	5.8	-		
Turn-On Rise Time	tr		-	25.7	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>		-	41	-		
Turn-Off Fall Time	tf	R <sub>G</sub> =012	-	31	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			_	_	1	Α	
Diode Forward Current	I <sub>S</sub>		_		'	^	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.85	1.2	V	

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.





#### **TYPICAL CHARACTERISTIC CURVES**

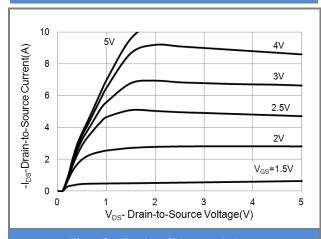


Fig.1 On-Region Characteristics

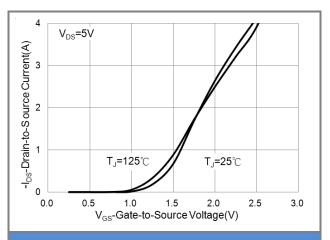


Fig.2 Transfer Characteristics

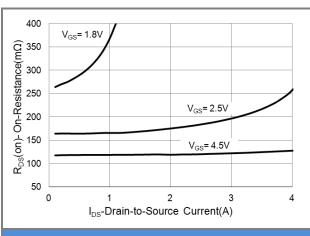


Fig.3 On-Resistance vs. Drain Current

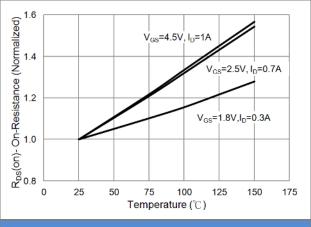


Fig.4 On-Resistance vs. Junction temperature

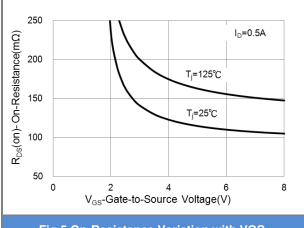


Fig.5 On-Resistance Variation with VGS.

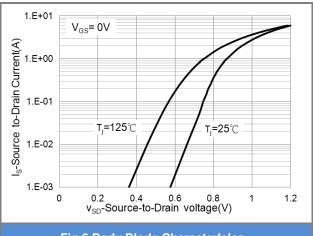


Fig.6 Body Dlode CharacterIslcs





### **TYPICAL CHARACTERISTIC CURVES**

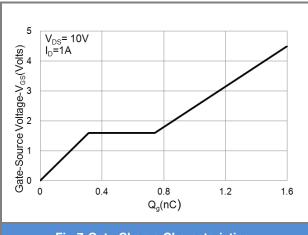


Fig.7 Gate-Charge Characteristics

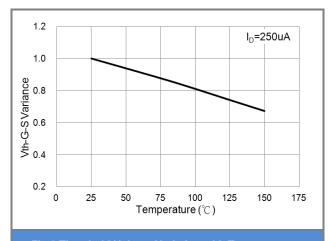


Fig.8 Threshold Voltage Variation with Temperature.

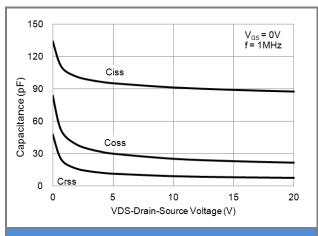


Fig.9 Capacitance vs. Drain-Source Voltage.

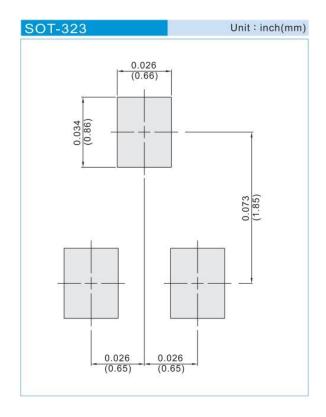




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJC7404_R1_00001	SOT-323	3K pcs / 7" reel	C04	Halogen free
PJC7404_R2_00001	SOT-323	12K pcs / 13" reel	C04	Halogen free

### **MOUNTING PAD LAYOUT**







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